

IN THE CLAIMS:

Please note that all claims currently pending and under consideration in the referenced application are shown below, in clean form, for clarity.

Please amend the claims as follows:

16. (Twice Amended) A method for forming an overlay target including a series of raised lines, the method comprising:  
providing a substrate;  
depositing a resist layer over said substrate;  
patterning said resist layer to include a resist pattern defining said overlay target including a series of raised lines;  
etching said substrate to form said overlay target including said resist pattern with said series of raised lines; and  
depositing a second layer of material having an upper surface thereof substantially free of depressions in the portion thereof covering said overlay target in said substrate.

17. (Previously Amended) The method of claim 16, wherein said providing a substrate comprises providing a semiconductor substrate selected from a group consisting of silicon, gallium, and sapphire substrates.

18. (Previously Amended) The method of claim 17, wherein said depositing a resist layer over said substrate comprises depositing a resist layer directly over said semiconductor substrate selected from the group consisting of silicon, gallium, and sapphire substrates.

19. (Previously Amended) The method of claim 16, wherein said providing a substrate includes providing a semiconductor substrate having a top surface, a bottom surface, and a material layer deposited over said top surface.

20. (Previously Amended) The method of claim 19, wherein said depositing a resist layer over said substrate comprises depositing a resist layer over said material layer and said etching said substrate to form said overlay target including a series of raised lines comprises etching said material layer.

21. (Previously Amended) The method of claim 16, wherein said etching comprises wet etching said substrate to form said overlay target including said resist pattern with said series of raised lines.